

Title (en)

HIGHLY OXYGEN-SENSITIVE SILICON LAYER AND METHOD FOR OBTAINING SAME

Title (de)

HOCHSAUERSTOFFEMPFLINDLICHE SILIZIUMSCHICHT UND VERFAHREN ZU IHRER HERSTELLUNG

Title (fr)

COUCHE DE SILICIUM TRES SENSIBLE A L'OXYGENE ET PROCEDE D'OBTENTION DE CETTE COUCHE

Publication

EP 1900012 A1 20080319 (FR)

Application

EP 06764054 A 20060704

Priority

- EP 2006063856 W 20060704
- FR 0552059 A 20050705

Abstract (en)

[origin: WO2007003638A1] The invention concerns a highly oxygen-sensitive silicon layer and a method for obtaining same. Said layer (2), formed on a substrate (4) for example made of SiC, has a 3x2 structure. The method for obtaining same consists in depositing silicon substantially uniformly on one surface of the substrate. The invention is applicable for example in microelectronics.

IPC 8 full level

H01L 21/28 (2006.01)

CPC (source: EP US)

H01L 21/049 (2013.01 - EP US); **H01L 21/28229** (2013.01 - EP US)

Citation (search report)

See references of WO 2007003638A1

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC NL PL PT RO SE SI SK TR

DOCDB simple family (publication)

FR 2888398 A1 20070112; FR 2888398 B1 20071221; EP 1900012 A1 20080319; JP 2008544945 A 20081211; US 2009294776 A1 20091203; WO 2007003638 A1 20070111

DOCDB simple family (application)

FR 0552059 A 20050705; EP 06764054 A 20060704; EP 2006063856 W 20060704; JP 2008519928 A 20060704; US 98834306 A 20060704